



NVUF Series

2~5KV; 20~50mA; 50nS

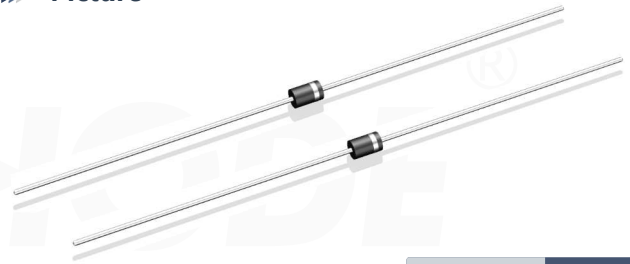
High Voltage Rectifier Diodes

NVUF Series Ultra Fast Recovery Night Vision Rectifier Diodes

Product Features

- ▶ Axial leaded connection.
- ▶ High thermal conductivity epoxy hot injection molding
- ▶ Excellent discharge characteristics.
- ▶ Fast reverse recovery time for high efficiency.
- ▶ Reverse leakage current is in the nanoampere range;
- ▶ Ultra small size packaging.

Picture



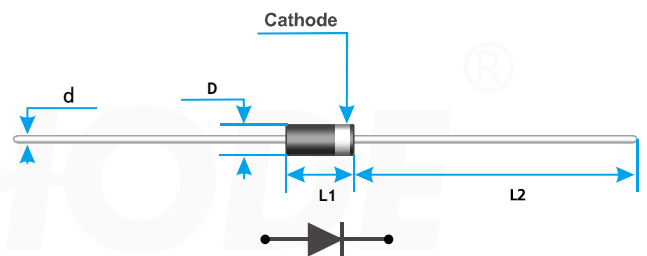
Package.No: HVD-203

Main Parameters

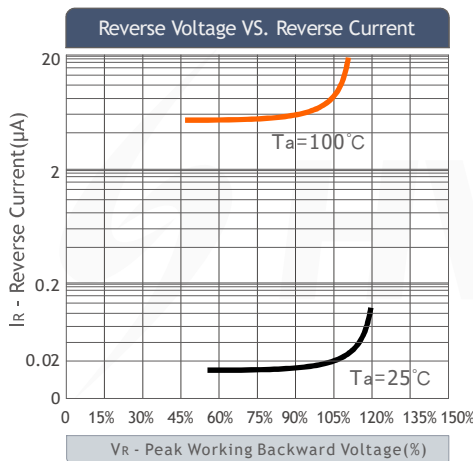
Type Code	V _{RWM} (KV)	I _F (mA)	V _F (V)	I _{FSM} (A)	T _{RR} (nS)	I _R (uA)
NV2UF20	2	20	9.0	3	50	0.02
NV3UF20	3	20	9.0	3	50	0.02
NV4UF20	4	20	9.0	3	50	0.02
NV5UF20	5	20	9.0	3	50	0.02
NV2UF50	2	50	8.0	5	50	0.02
NV3UF50	3	50	8.0	5	50	0.02
NV4UF50	4	50	8.0	5	50	0.02
NV5UF50	5	50	8.0	5	50	0.02

Dimensions

Fig.NO ①



Curve



Package Size

Package.No	D	d	L1	L2
HVD-203	φ 2.0/0.079	φ 0.5/0.02	3.0/0.118	25/0.98

About Tolerance: [±0.2mm/0.01inch] Except [L2±0.5mm/0.02inch]

Other Characteristic Parameters & Test Conditions

PARAMETER NAME	SYMBOL	TEST CONDITIONS	UNIT
Max Peak Working Backward Voltage	V _{RWM}	T _A =25°C I _R =0.02μA	KV
Average Forward Rectified Current	I _{F(AV)}	T _A =50°C In air	mA
Max Forward Peak Voltage	V _F	@ T _A =25°C I _F =I _F	V
Max Surge Forward Current	I _{FSM}	50Hz Half-sine Wave, Resistance load@T _{Break} =50°C	A
Max Reverse Recovery Time	T _{RR}	I _F = 2mA; I _R = -4mA; I _{RR} = -1mA	nS
Max Reverse Leakage Current	I _R	T _A = 25°C V _R =V _{RWM}	uA
Junction Temperature(MAX)	T _J	-55°C~150°C	°C
Storage Temperature	T _{STG}	-55°C~125°C	°C